

GSM4804

40V N-Channel Enhancement Mode MOSFET

Product Description

GSM4804, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge. These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

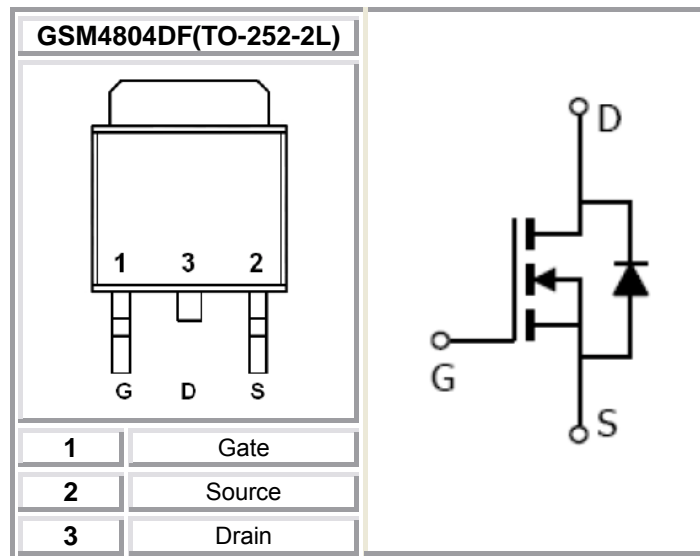
Features

- 40V/16A, $R_{DS(ON)} = 48m\Omega @ V_{GS} = 10V$
- 40V/10A, $R_{DS(ON)} = 70m\Omega @ V_{GS} = 4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- TO-252-2L package design

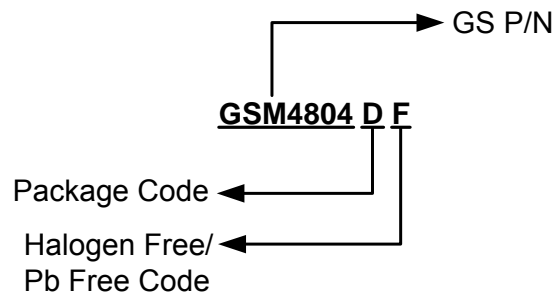
Applications

- Backlight Inverter for LCD Display
- Full Bridge DC/DC Converter

Packages & Pin Assignments

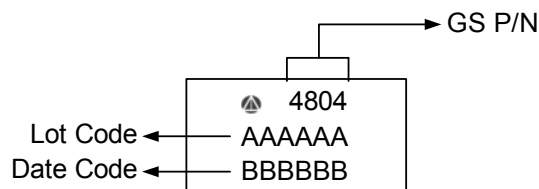


Ordering Information



Part Number	Package	Quantity Reel
GSM4804DF	TO-252-2L	2500 PCS

Marking Information



Absolute Maximum Ratings

(T_A=25°C unless otherwise noted)

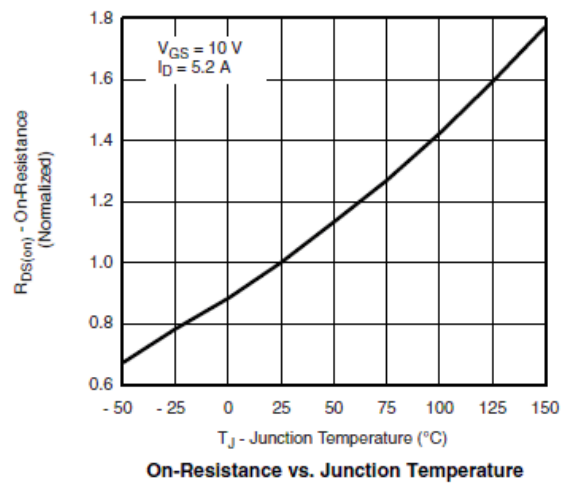
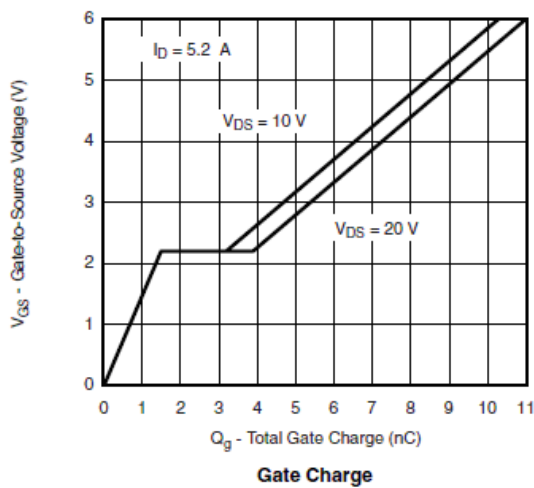
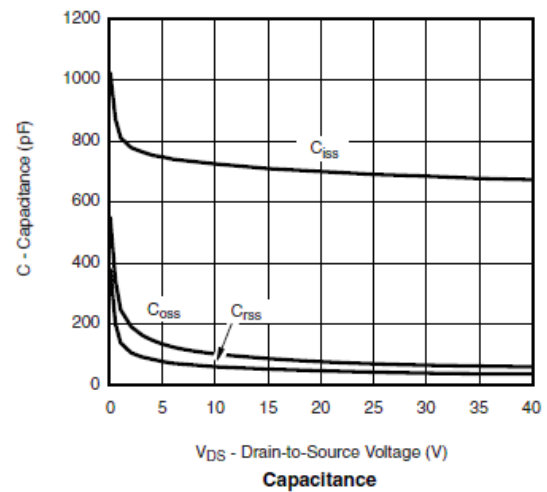
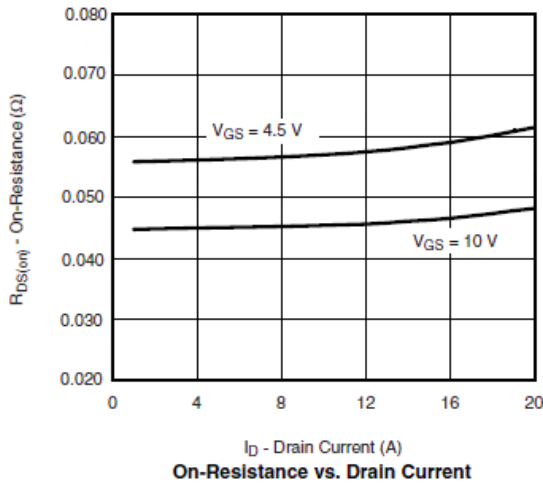
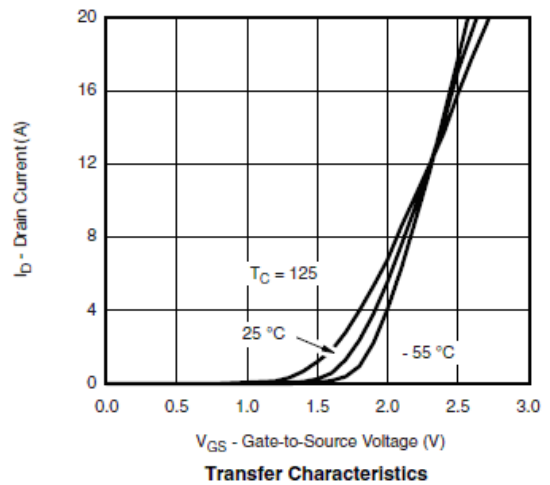
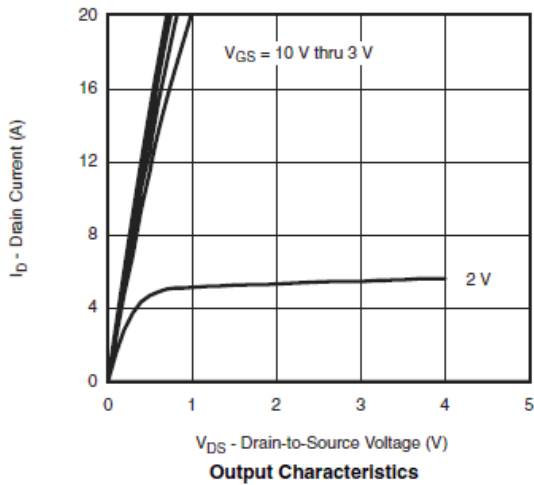
Symbol	Parameter	Typical	Unit	
V _{DSS}	Drain-Source Voltage	40	V	
V _{GSS}	Gate –Source Voltage	±20	V	
I _D	Continuous Drain Current(T _J =150°C)	T _A =25°C	18	A
		T _A =70°C	15	
I _{DM}	Pulsed Drain Current	40	A	
I _S	Continuous Source Current(Diode Conduction)	8	A	
I _{AS}	Single Pulse Avalanche Current	L=0.1mH	25	A
E _{AS}	Avalanche Energy		35	mJ
P _D	Power Dissipation	T _A =25°C	40	W
		T _A =70°C	15	
T _J	Operating Junction Temperature	150	°C	
T _{STG}	Storage Temperature Range	-55/150	°C	
R _{θJA}	Thermal Resistance-Junction to Ambient	62.5	°C/ W	

Electrical Characteristics

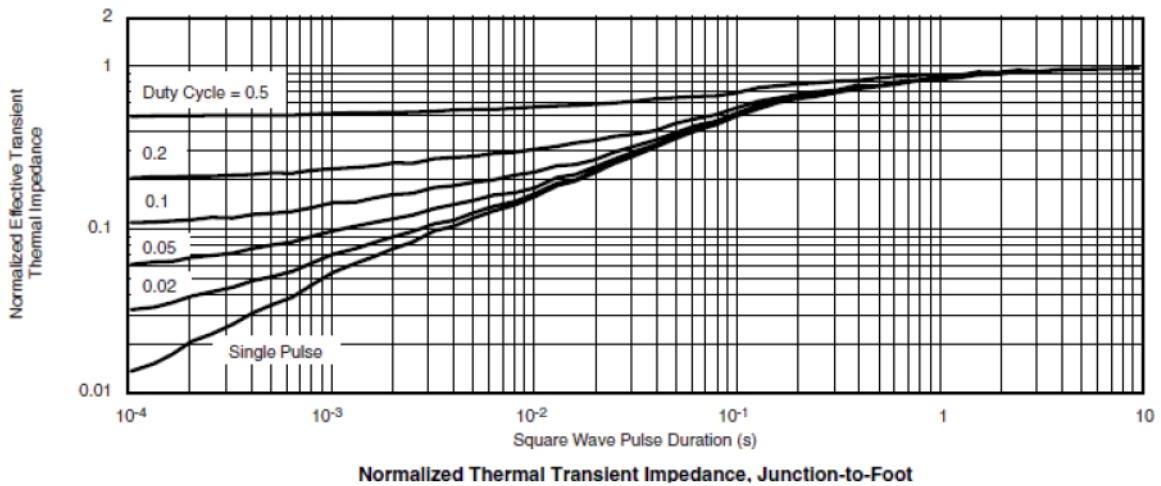
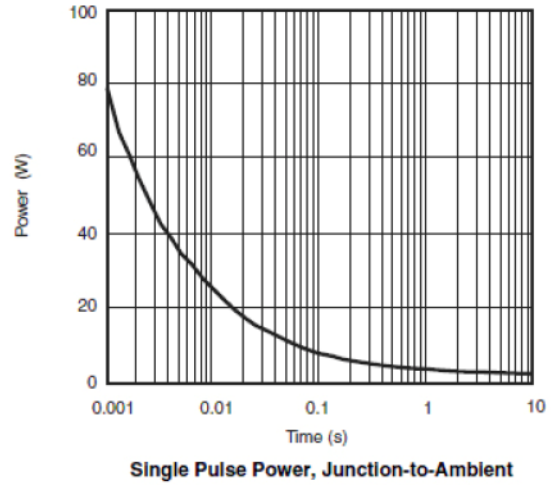
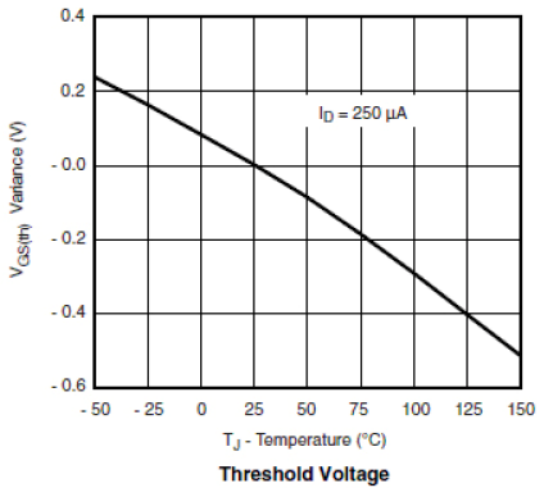
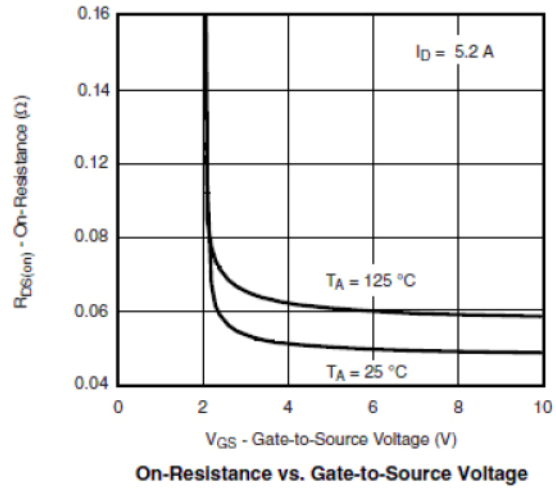
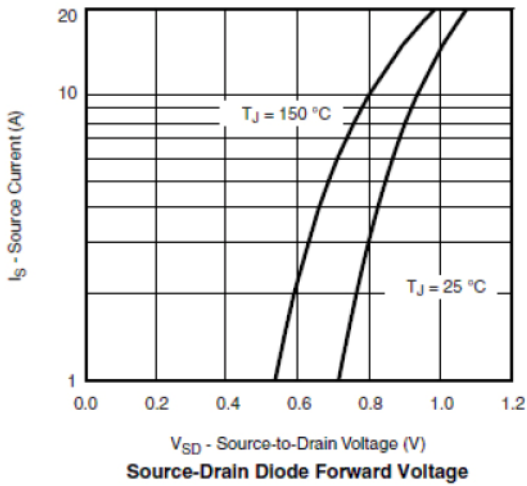
($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ	Max.	Unit
Static						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		2.0	
I_{GSS}	Gate Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=40V, V_{GS}=0V$			1	uA
		$V_{DS}=40V, V_{GS}=0V, T_J=85^{\circ}\text{C}$			10	
$I_{D(on)}$	On-State Drain Current	$V_{DS}\geq 5V, V_{GS}=10V$	10			A
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V, I_D=16A$		42	48	m Ω
		$V_{GS}=4.5V, I_D=10A$		56	70	
g_{fs}	Forward Transconductance	$V_{DS}=15V, I_D=5.0A$		25		S
V_{SD}	Diode Forward Voltage	$I_S=2A, V_{GS}=0V$		0.85	1.2	V
Dynamic						
C_{iss}	Input Capacitance	$V_{DS}=20V, V_{GS}=0V, f=1\text{MHz}$		850		pF
C_{oss}	Output Capacitance			110		
C_{riss}	Reverse Transfer Capacitance			75		
Q_g	Total Gate Charge	$V_{DS}=20V, V_{GS}=4.5V, I_D=5.0A$		10	14	nC
Q_{gs}	Gate-Source Charge			2.8		
Q_{gd}	Gate-Drain Charge			3.2		
$t_{d(on)}$	Turn-On Time	$V_{DD}=20V, R_L=4\Omega, I_D=5.0A, V_{GEN}=10V, R_G=1\Omega$		6	12	ns
T_r				10	20	
$t_{d(off)}$	Turn-Off Time			20	36	
T_f				6	12	

Typical Performance Characteristics

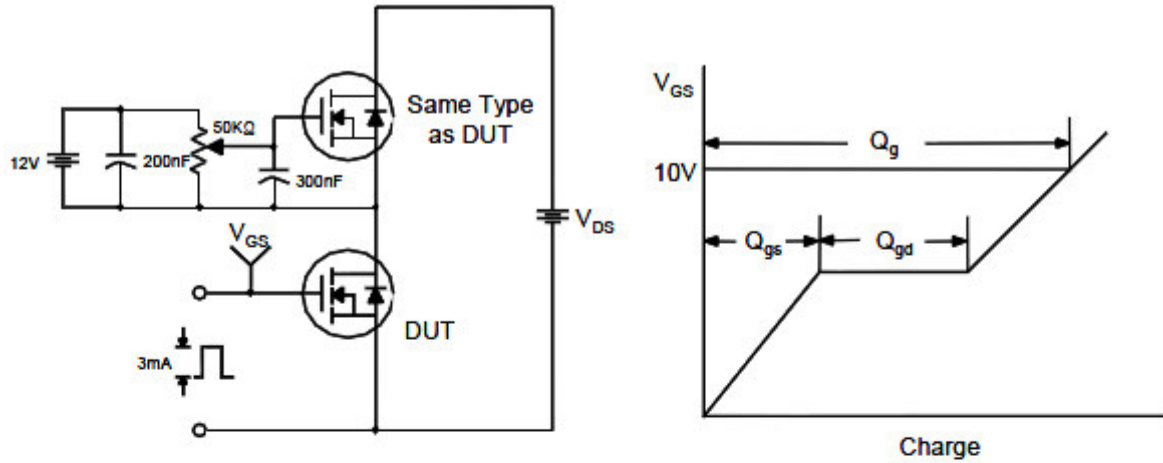


Typical Performance Characteristics (continue)

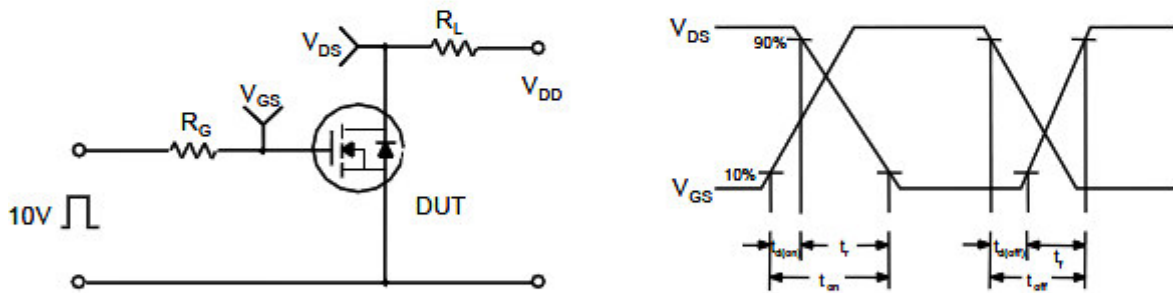


Typical Characteristics

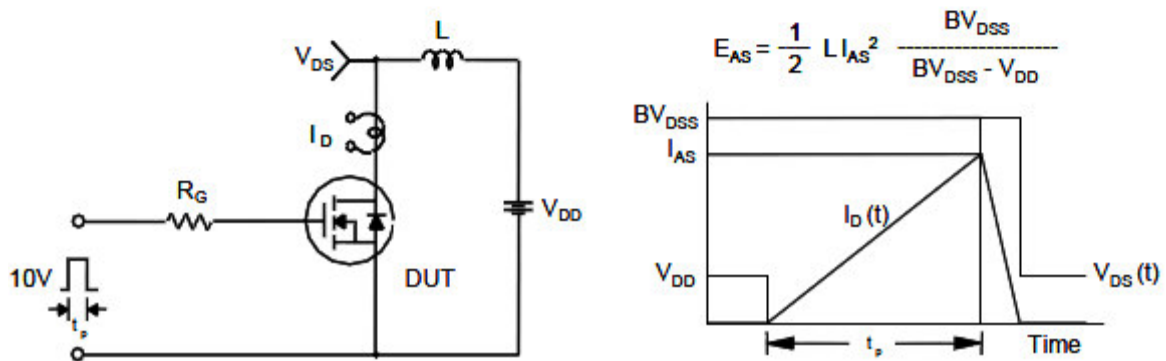
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

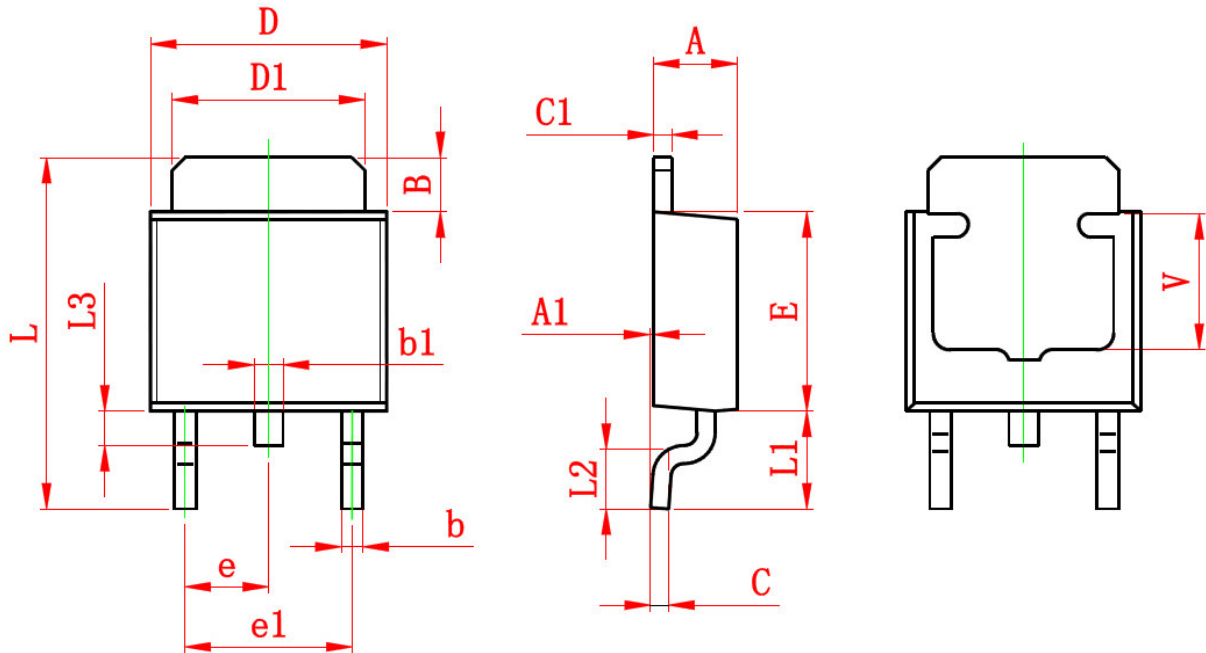


Unclamped Inductive Switching Test Circuit & Waveforms



Package Dimension

TO-252-2L PLASTIC PACKAGE











Dimensions				
SYMBOL	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF.		0.150 REF.	



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CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

Wu-Xi Branch	
	No.21 Changjiang Rd., WND, Wuxi, Jiangsu, China (INFO. &. TECH. Science Park Building A 210 Room)
	86-510-85217051
	86-510-85211238
	sales_cn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587